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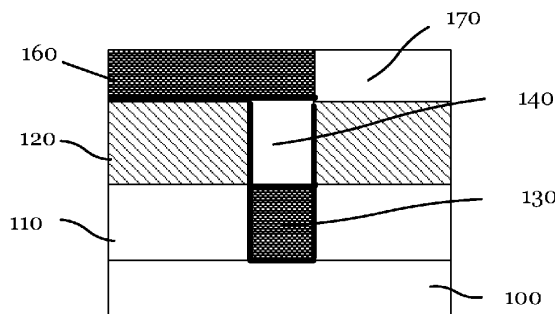


FIG. 1E

(57) Abstract: A method of processing a substrate includes forming an amorphous silicon (aSi) layer over the substrate, where the substrate includes a dielectric layer and a conductive layer, and the a-Si liner covers a surface of the dielectric layer and a surface of the conductive layer. The method includes converting the a-Si liner into a silicon-containing layer including a metal; and depositing the metal over the silicon-containing layer using the silicon-containing layer as a seed layer for the depositing, where the metal deposited over the silicon-containing layer and the conductive layer are electrically connected.



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